

Features

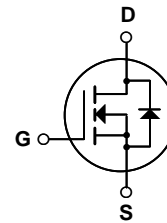
- 95A, 30V, $R_{DS(on)} = 0.0085\Omega$ @ $V_{GS} = 10V$
- Low gate charge (typical 36 nC)
- Low Crss (typical 240 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability
- 175°C maximum junction temperature rating

General Description

These N-Channel enhancement mode power field effect transistors are produced using Kersemi proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for low voltage applications such as DC/DC converters, high efficiency switching for power management in portable and battery operated products.

TO-220



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	KSM95N03L	Units
V_{DSS}	Drain-Source Voltage	30	V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$) - Continuous ($T_C = 100^\circ\text{C}$)	95	A
		67.2	A
I_{DM}	Drain Current - Pulsed (Note 1)	380	A
V_{GSS}	Gate-Source Voltage	± 20	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	400	mJ
I_{AR}	Avalanche Current (Note 1)	95	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	15	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	7.0	V/ns
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$) - Derate above 25°C	150	W
		1.0	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +175	$^\circ\text{C}$
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typ	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	1.0	$^\circ\text{C/W}$
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink	0.5	--	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	62.5	$^\circ\text{C/W}$

Electrical Characteristics
 $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	30	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to 25°C	--	0.03	--	V/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$	--	--	1	μA
		$V_{DS} = 24\text{ V}, T_C = 150^\circ\text{C}$	--	--	10	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -20\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	1.0	--	2.5	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 47.5\text{ A}$	--	0.0069	0.0085	Ω
		$V_{GS} = 5\text{ V}, I_D = 47.5\text{ A}$	--	0.009	0.0115	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 15\text{ V}, I_D = 47.5\text{ A}$ (Note 4)	--	57	--	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	1750	2280	pF
C_{oss}	Output Capacitance		--	1080	1400	pF
C_{rss}	Reverse Transfer Capacitance		--	240	310	pF

Switching Characteristics

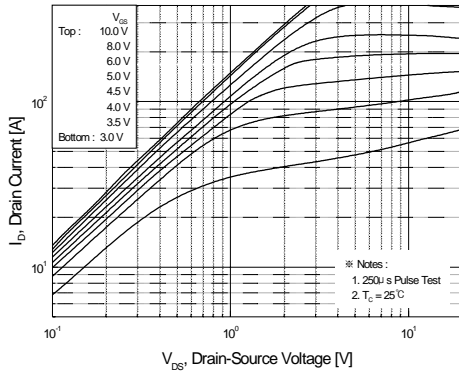
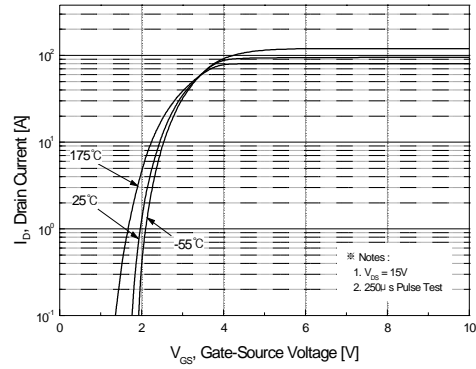
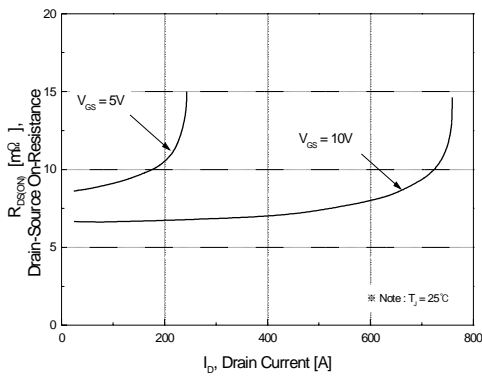
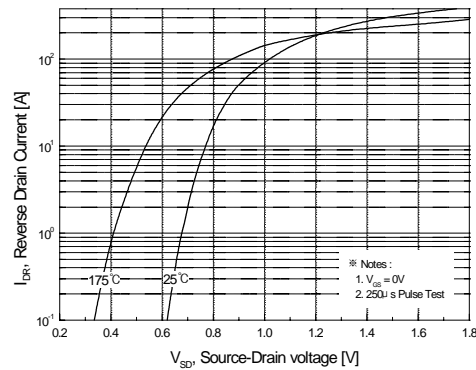
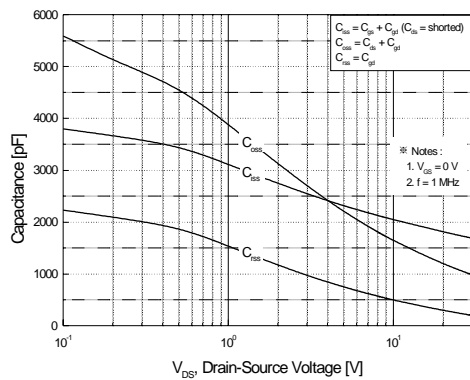
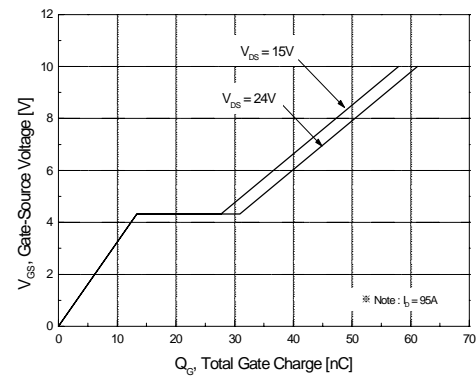
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 15\text{ V}, I_D = 47.5\text{ A},$ $R_G = 25\ \Omega$	--	25	60	ns
t_r	Turn-On Rise Time		--	250	510	ns
$t_{d(off)}$	Turn-Off Delay Time		--	18	45	ns
t_f	Turn-Off Fall Time		(Note 4, 5)	--	135	280
Q_g	Total Gate Charge	$V_{DS} = 24\text{ V}, I_D = 95\text{ A},$ $V_{GS} = 5\text{ V}$	--	36	47	nC
Q_{gs}	Gate-Source Charge		--	13.4	--	nC
Q_{gd}	Gate-Drain Charge		(Note 4, 5)	--	17.6	--

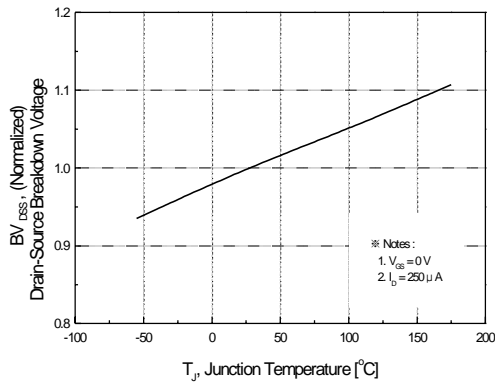
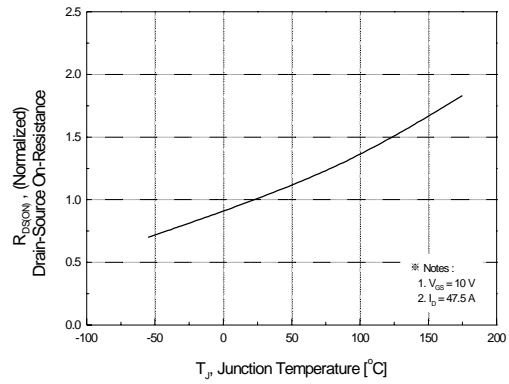
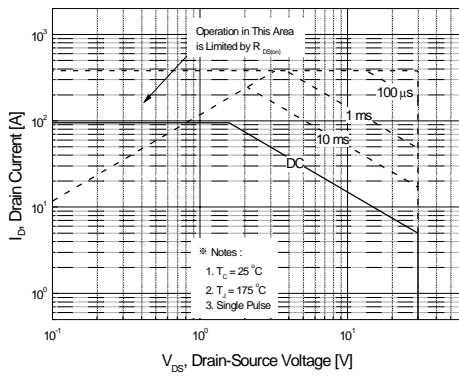
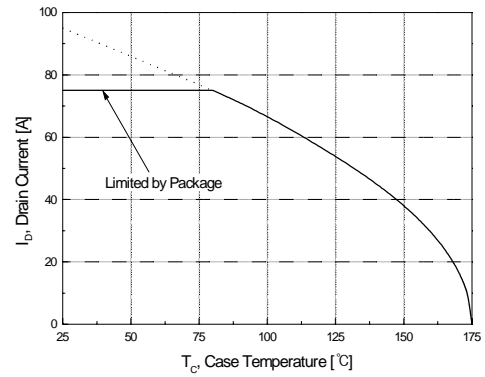
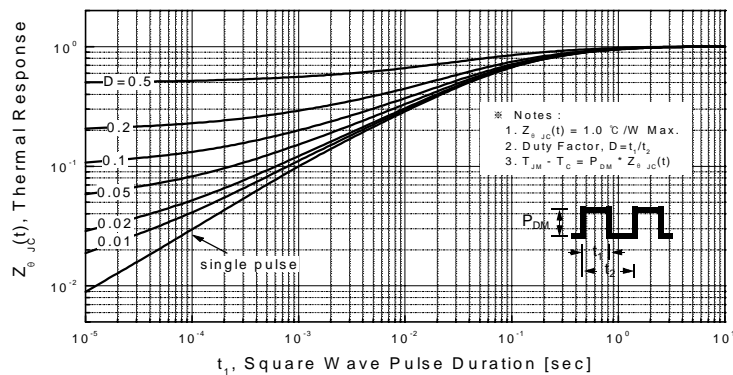
Drain-Source Diode Characteristics and Maximum Ratings

I_S	Maximum Continuous Drain-Source Diode Forward Current	--	--	95	A	
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current	--	--	380	A	
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 95\text{ A}$	--	--	1.5	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = 95\text{ A},$	--	55	--	ns
Q_{rr}	Reverse Recovery Charge	$di_F / dt = 100\text{ A}/\mu\text{s}$ (Note 4)	--	65	--	nC

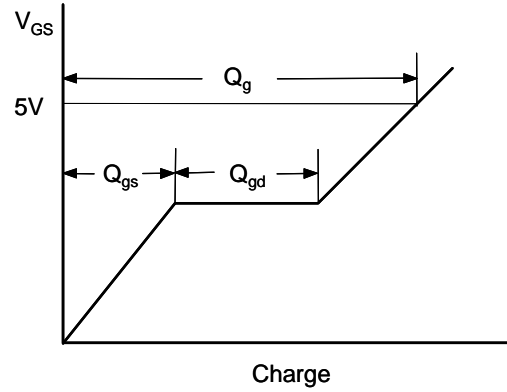
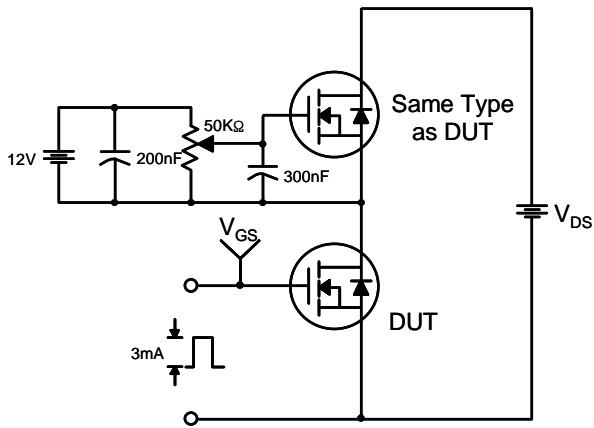
Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $L = 45\ \mu\text{H}, I_{AS} = 95\text{ A}, V_{DD} = 15\text{ V}, R_G = 25\ \Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 95\text{ A}, di/dt \leq 300\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width $\leq 300\ \mu\text{s}$, Duty cycle $\leq 2\%$
5. Essentially independent of operating temperature
6. Continuous Drain Current Calculated by Maximum Junction Temperature : Limited by Package

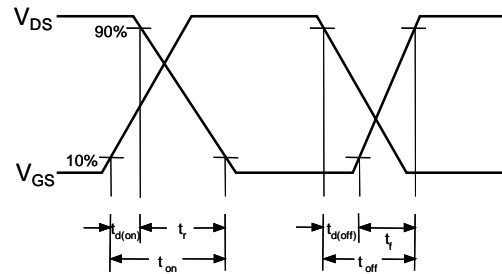
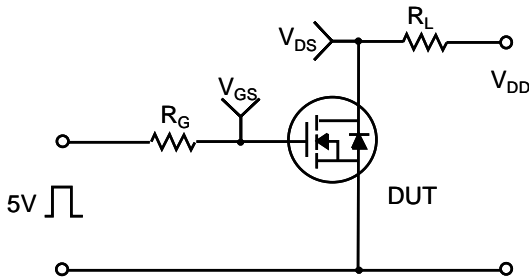
Typical Characteristics

Figure 1. On-Region Characteristics

Figure 2. Transfer Characteristics

Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

Figure 5. Capacitance Characteristics

Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

Figure 8. On-Resistance Variation vs. Temperature

Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature

Figure 11. Transient Thermal Response Curve

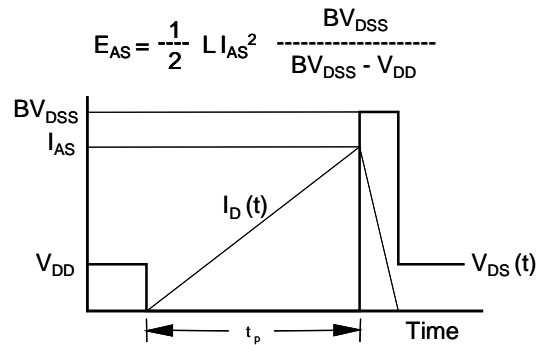
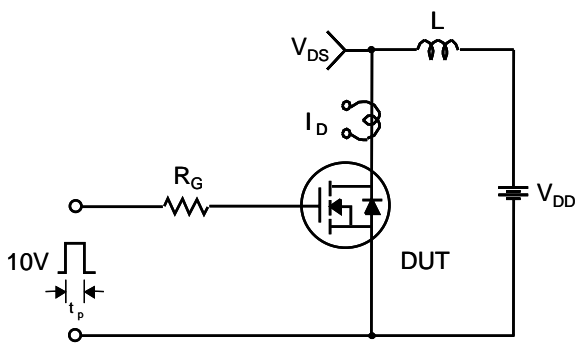
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms



Peak Diode Recovery dv/dt Test Circuit & Waveforms
